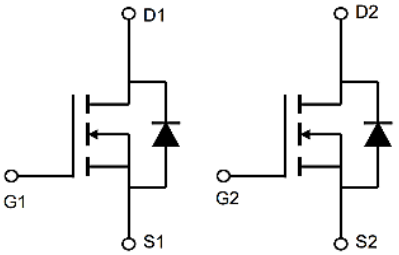
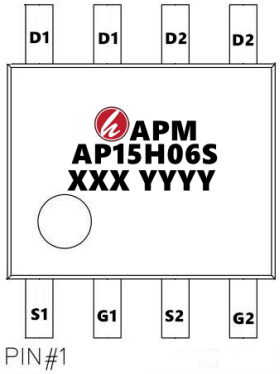
AP15H06S

60V N+N-Channel Enhancement Mode MOSFET

Description

The AP15H06S uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.





General Features

V_{DS} = 60V I_D =15A

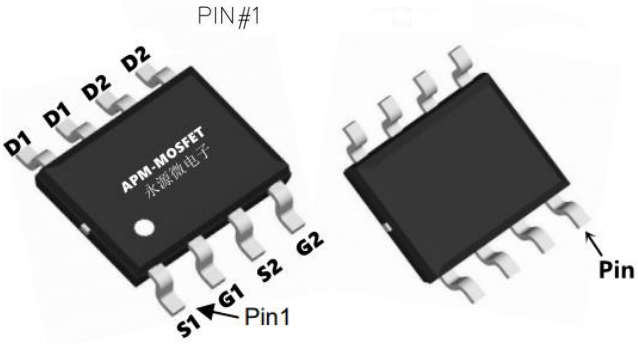
$R_{DS(ON)}$ < 18mΩ @ V_{GS}=10V (Type：11mΩ)

Application

Battery protection

Load switch

Uninterruptible power supply



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP15H06S	SOP-8L	AP15H06S XXX YYYY	3000

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	60	V
VGS	Gate-Source Voltage	±20	V
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	15	A
I_D@T_A=70℃	Continuous Drain Current, V_{GS} @ 10V[1]	9.2	A
IDM	Pulsed Drain Current[2]	45	A
EAS	Single Pulse Avalanche Energy[3]	64	mJ
P_D@T_A=25℃	Total Power Dissipation[4]	3.6	W
TSTG	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
$R_{\theta}JA$	Thermal Resistance Junction-Ambient [1]	85	℃/W

60V N+N-Channel Enhancement Mode MOSFET

Electrical Characteristics (T_J=25℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	60	65	---	V
△BVDSS/△TJ	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.057	---	V/℃
RDS(ON)	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=12A	---	11	18	mΩ
		V_{GS}=4.5V , I_D=10A	---	15	20	
VGS(th)	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	1.6	2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.68	---	mV/℃
IDSS	Drain-Source Leakage Current	V_{DS}=48V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=48V , V_{GS}=0V , T_J=55℃	---	---	5	
IGSS	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=15A	---	45	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	1.7	---	Ω
Q_g	Total Gate Charge (4.5V)	V_{DS}=48V , V_{GS}=4.5V , I_D=15A	---	19.3	---	nC
Q_{gs}	Gate-Source Charge		---	7.1	---	
Q_{gd}	Gate-Drain Charge		---	7.6	---	
Td(on)	Turn-On Delay Time	V_{DD}=30V , V_{GS}=10V , R_G=3.3Ω, I_D=15A	---	7.2	---	ns
T_r	Rise Time		---	50	---	
Td(off)	Turn-Off Delay Time		---	36.4	---	
T_f	Fall Time		---	7.6	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	2423	---	pF
Coss	Output Capacitance		---	145	---	
Crss	Reverse Transfer Capacitance		---	97	---	
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	35	A
ISM	Pulsed Source Current[2,5]		---	---	80	A
VSD	Diode Forward Voltage[2]	V_{GS}=0V , I_S=A , T_J=25℃	---	---	1	V
t_{rr}	Reverse Recovery Time	IF=15A , dI/dt=100A/μs , T_J=25℃	---	16.3	---	nS
Q_{rr}	Reverse Recovery Charge		---	11	---	nC

Notes:

1、The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2、The data tested by pulsed , pulse width .The EAS data shows Max. rating .
3、The power dissipation is limited by 175℃ junction temperature
4、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Typical Characteristics

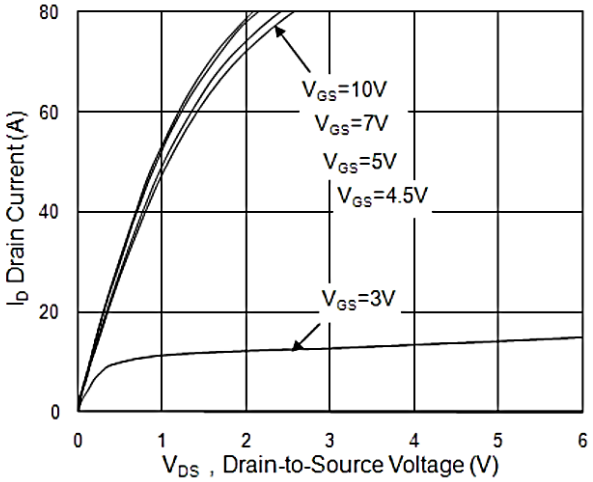


Fig.1 Typical Output Characteristics

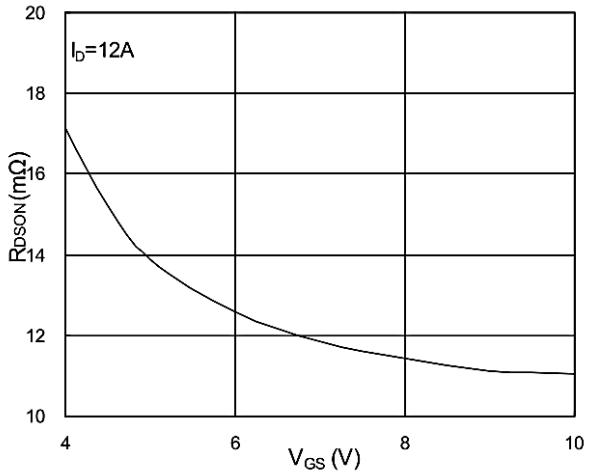


Fig.2 On-Resistance v.s Gate-Source

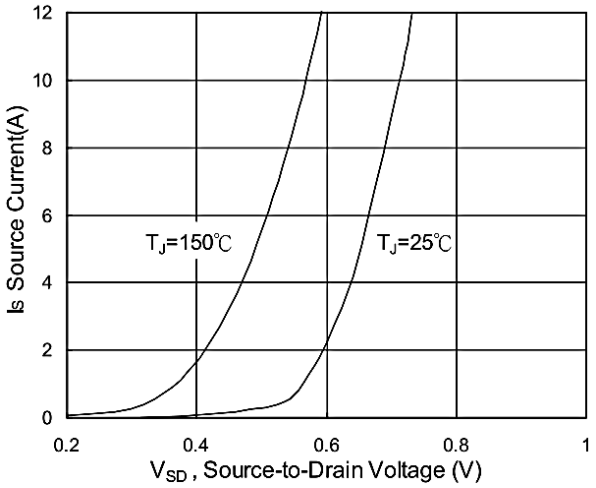


Fig.3 Forward Characteristics of Reverse

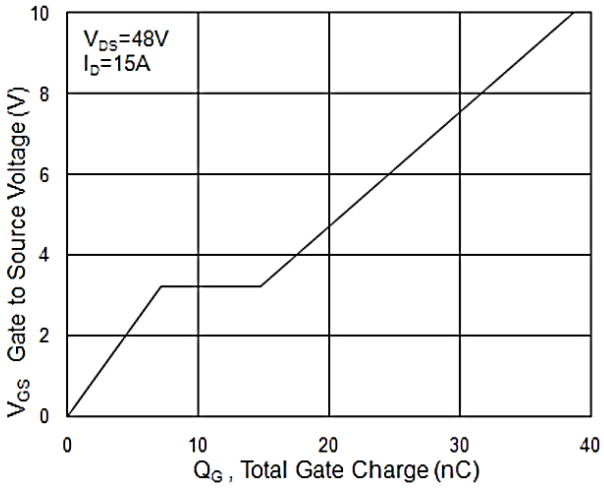


Fig.4 Gate-Charge Characteristics

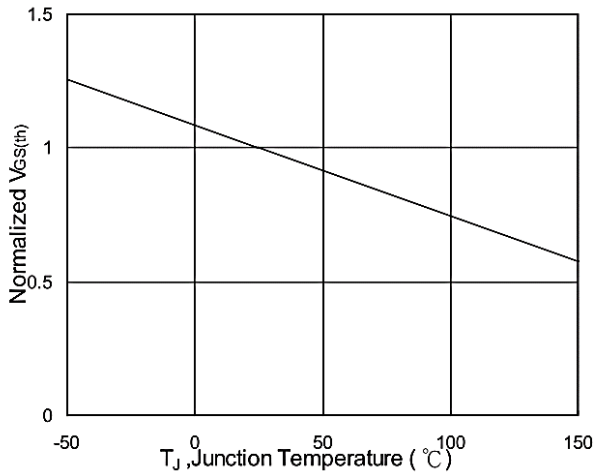


Fig.5 Normalized V_{GS} v.s T_J

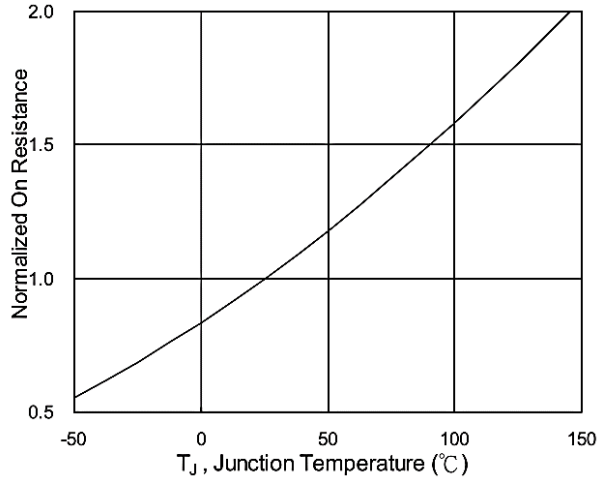


Fig.6 Normalized R_{DSON} v.s T_J

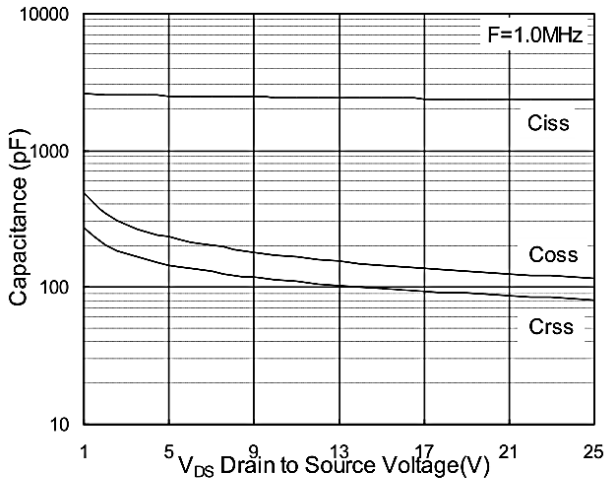


Fig.7 Capacitance

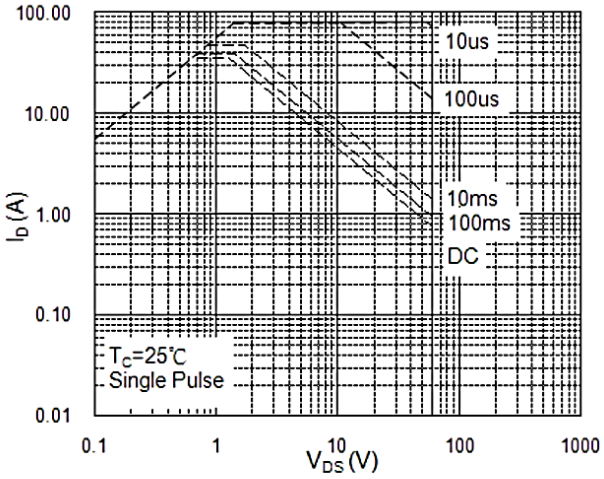


Fig.8 Safe Operating Area

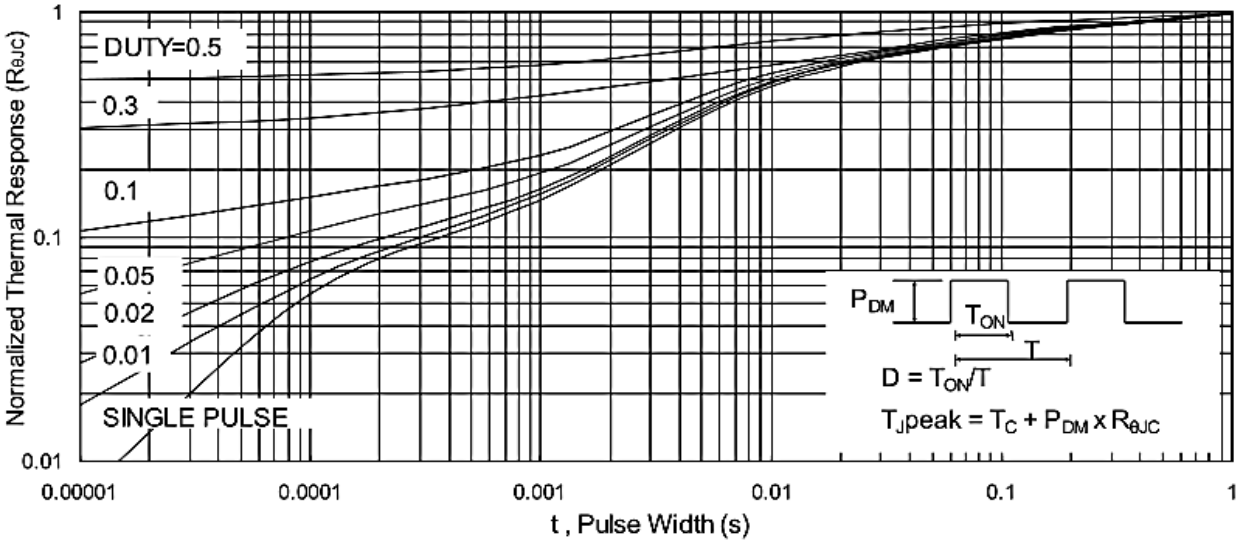


Fig.9 Normalized Maximum Transient Thermal Impedance

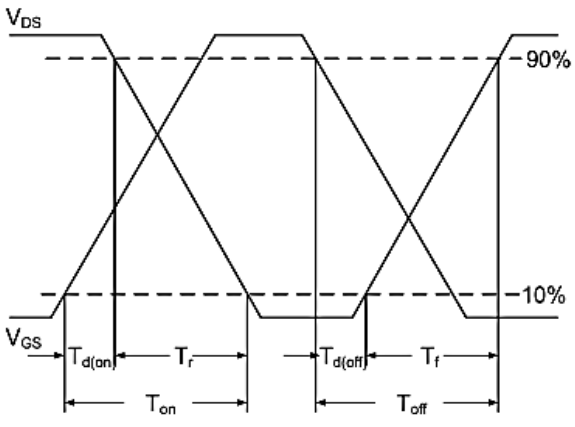


Fig.10 Switching Time Waveform

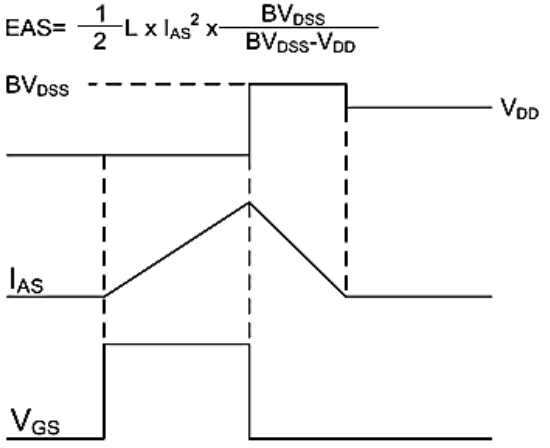
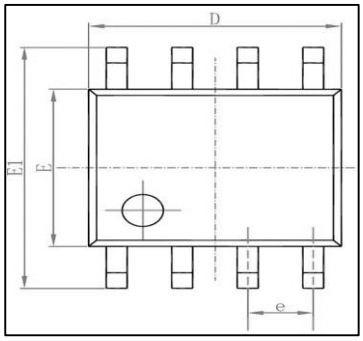
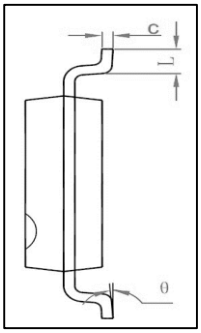
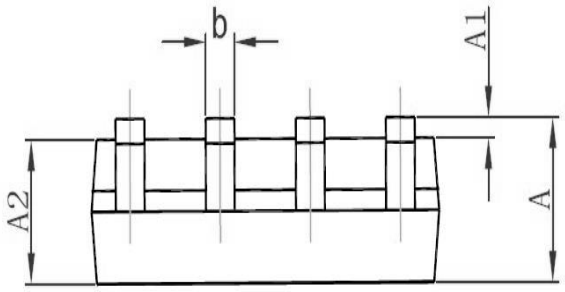


Fig.11 Unclamped Inductive Switching Waveform

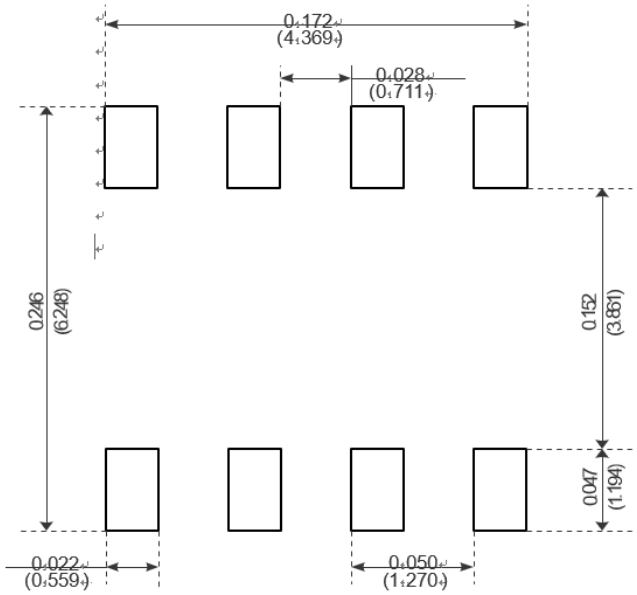
Package Mechanical Data-SOP-8L-DX-Double







Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



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Edition	Date	Change
Rve1.0	2020/12/1	Initial release